

FORM PTO 1449 (modified)			ATTY DOCKET NO. BHT/3230-56		APPLICATION NO. 10/601,701		
U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE			APPLICANT YEH				
LIST OF REFERENCES CITED BY APPLICANT(S) (Use several sheets if necessary)							
Date Submitted to PTO: October 20, 2003			FILING DATE Jun 24, 2003		GROUP 2812		
U.S. PATENT DOCUMENTS							
	DOCUMENT NUMBER	DATE	NAME	CLASS	subclass	FILING DATE IF APPROPRIATE	
	4,330,363	05/18/82	Biegesen et al.				
	4,592,799	06/03/86	Hayafuji				
	5,021,119	06/04/91	Fan et al.				
	5,395,481	03/07/95	McCarthy				
	6,495,405 B2	12/17/02	Voutsas et al.				
FOREIGN PATENT DOCUMENTS							
	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	subclass	TRANSLATION YES/NO/ OR ABSTRACT	
OTHER DOCUMENT(S) (Including Author, Title, Date, Pertinent Pages, Etc.)							
SDS	<p><b>High-Performance Low-Temperature Poly-Si TFTs Crystallized by Excimer Laser with Recessed-Channel Structure, Lin et al., IEEE Electron Device Letters, Vol. 22, No. 6, June 2001, pages 269-271</b></p>						
	<p><b>Performance Improvement Obtained for Thin-Fil Transistors Fabricated in Prepatterned Laser-Recrystallized Polysilicon, Giust et al., IEEE Electron Device Letters, Vol. 18, No. 6, June 1997, pages 296-298</b></p>						
	<p><b>Comparison of excimer laser recytstallized prepatterned and unpatterned silicon films on SiO<sub>2</sub>, Giust et al., J.Appl.Phys. 81(3), 1 February 1997, pages 1204-1211</b></p>						
	<p><b>High-Performance Single Crystalline-Silicon TFTs on a Non-Alkali Glass Substrate, Sano et al. Fujitsu Laboratories Ltd., Atsugi 243-0197, Japan (C) 2002 IEEE</b></p>						
EXAMINER				DATE CONSIDERED		12/09/04	

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.